

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor device includes the steps of: forming an insulating film on a conductive pattern formed on a substrate; forming a resist pattern on the insulating film; performing etching to the insulating film using the resist pattern as a
5 mask to form in the insulating film an opening at which part of the surface of the conductive pattern is exposed; forming an antioxidant layer on the part of surface of the conductive pattern exposed while removing the resist pattern; and depositing a conductive film on the conductive pattern from which the antioxidant layer has been removed.